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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/663,774	09/17/2003	Kyoung Mook Lee	8733.915.00-US	1766

30827 7590 08/09/2005

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EXAMINER	
WANG, GEORGE Y	

ART UNIT	PAPER NUMBER
2871	

DATE MAILED: 08/09/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/663,774	LEE ET AL.	
	Examiner	Art Unit	
	George Y. Wang	2871	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on *26 May 2005*.

2a)☒ This action is **FINAL**. 2b)☐ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *1-30* is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☒ Claim(s) *1-30* is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☒ The drawing(s) filed on *17 September 2003* is/are: a)☒ accepted or b)☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☒ All b)☐ Some * c)☐ None of:

1.☒ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____.

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☐ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.
4) ☐ Interview Summary (PTO-413) Paper No(s)/Mail Date. _____.
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: _____.

DETAILED ACTION

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

> (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

2. Claims 1-5, 7-19, and 23-30 are rejected under 35 U.S.C. 103(a) as being unpatentable over Song et al. (U.S. Patent No. 6,215,541, hereafter "Song") in view of Ozaki et al. (U.S. Patent No. 6,184,947, hereafter "Ozaki").

3. As to claims 1 and 8, Song discloses an array substrate for a liquid crystal display (LCD) device (Fig. 5) a substrate (100), a gate line (20) and a thin film transistor having a gate electrode (21), a source electrode (61), a drain electrode (62) and an

active layer (40) formed over the substrate (100), an interlayer insulating layer (30) formed on the thin film transistor, a first gate redundancy line (fig. 5, ref. 64) formed on the interlayer insulating layer, and connected electrically with one of the gate electrode (21), the gate line (20), and both the gate electrode (20) and gate line (20) through a first gate contact hole (75). Song also discloses a passivation layer (70) provided on the first gate redundancy line and the interlayer insulating layer (30) and a pixel electrode (66) electrically connected with the drain electrode through the drain contact hole formed in the passivation layer (fig. 17b). Song teaches that the gate redundancy line is made of chromium, molybdenum or molybdenum alloy.

However, Song does not teach that the gate redundancy line is formed of the same material as one of the source and drain electrodes, which are made from a semiconductor material as, can be seen from Fig. 7.

Ozaki in disclosing thin film transistor matrix with repair bus lines teaches that the gate line (GL) can also be made of a semiconductor layer having a high impurity concentration (col. 3, lines 62-64).

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to adapt the gate line made from a semiconductor material (as taught by Ozaki) in place of metals such as chromium, molybdenum or molybdenum alloy (as taught by Song) to avoid pin holes that might be formed in the metal layers and to repair any breakage in the metal layer (col. 2, lines 49-56).

4. As to claims 2-5, 7 and 9-13, Song teaches the thin film transistor as a bottom gate thin film transistor, the first gate contact hole (75) is formed passing through the interlayer insulating layers and also teaches a second gate contact hole for connection of the first gate redundancy line with the gate line (Fig. 5) and (col. 6, lines 1-9). Ozaki teaches that the thin film transistor can also be a top gate thin film transistor (Fig. 1D).

5. As to claims 14 and 24, Song discloses the method of fabricating the array substrate for a liquid crystal display in (col. 11, lines 13-67), (col. 12, lines 1-67) and (col. 1 3,lines 1-10). The method comprises forming a gate line and a gate electrode on a substrate, forming an interlayer insulating layer on the gate line and the gate electrode, forming a thin film transistor with the gate electrode, a source electrode, a drain electrode, and an active layer, forming a first gate redundancy line on the interlayer insulating layer electrically connected with one of the gate electrode, the gate line, and both the gate electrode and gate line through a first gate contact hole, forming a passivation layer on the first gate redundancy line and the interlayer insulating layer; and forming a drain contact hole in the passivation layer, and forming a pixel electrode connected electrically with the drain electrode through the drain contact hole.

6. As to claims 15-19, 23 and 25-30, Song teaches the array substrate for LCD as recited above where the formation of the thin film transistor is as a bottom gate thin film transistor, the first gate contact hole (75) is formed passing through the interlayer insulating layers and also teaches a second gate contact hole for connection of the first

gate redundancy line with the gate line (Fig. 5) and (col. 6, lines 1-9). Ozaki teaches that the formation of the thin film transistor as a top gate thin film transistor (Fig. 1D).

7. Claims 6 and 20-22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Song in view of Ozaki as applied to claims 1 and 14 above, and further in view of Huh et al. (U.S.Patent No. 6,307,216, hereafter "Huh").

Song, when modified by Ozaki discloses the array substrate for LCD as recited above, however, neither reference teaches the formation of a second gate line.

Huh in disclosing a thin film transistor panel for liquid crystal displays, teaches the use of a second gate line and electrical connection to the first gate line (col. 2, lines 26-43) and (col. 3, lines 45-67). Huh also teaches the contact holes (C1, C2 andc3) formed in the passivation film (30) and the material of the connect pattern is made of the same material as the pixel electrode (col. 4, lines 23-35).

Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to adapt the second gate line and its electrical connection to the first gate line as disclosed by Huh to the devise of Song in view of Ozaki to provide a redundancy line structure used for effectively repair disconnection defects without introducing additional steps and for preventing short-circuited defects between the upper and the lower substrates and between adjacent pixels (col. 1, lines 45-55).

Response to Arguments

8. Applicant's arguments filed May 26, 2005 have been fully considered but they are not persuasive.

Applicant's main argument is that the Song reference fails to specifically disclose a gate redundancy line formed of the same material as one of the source and drain electrodes. First, Applicant asserts that in Fig. 5, ref. 64 is not a gate redundancy line, but a data line connector. However, a gate redundancy line, in fact, serves as a data line "connector" by connecting data lines. Furthermore, with regard to Applicant's argument that the Ozaki reference does not disclose forming a gate line out of the same material as the source and drain, it is noted that Ozaki does disclose that the gate line is made of the same material of the semiconductor, to which the Song reference states is the same material used in the source and drain electrodes (Fig. 7). As a result, with regard to each of the independent claims, the Song reference, when modified by the Ozaki reference, clearly discloses that a gate line made of the same material as the source and drain electrodes would have been obvious to one having ordinary skill in the art at the time the invention was made to adapt the gate line made from a semiconductor material (as taught by Ozaki) in place of metals such as chromium, molybdenum or molybdenum alloy (as taught by Song) since one would be motivated to to avoid pin holes that might be formed in the metal layers and to repair any breakage in the metal layer (col . 2, lines 49-56). As a result, rejection is proper.

Conclusion

9. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to George Y. Wang whose telephone number is 571-272-2304. The examiner can normally be reached on M-F, 8 am - 4:30 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Robert H. Kim can be reached on 571-272-2293. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

gw
July 30, 2005

T. NGUYEN
PRIMARY EXAMINER